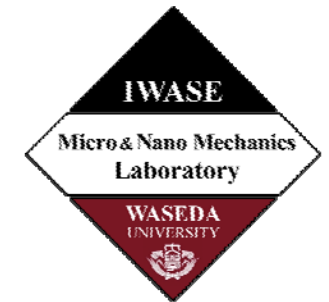


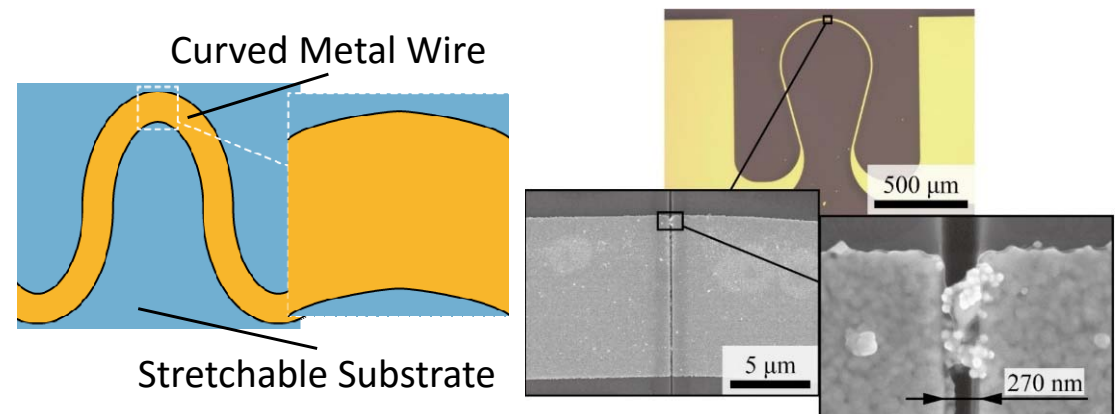
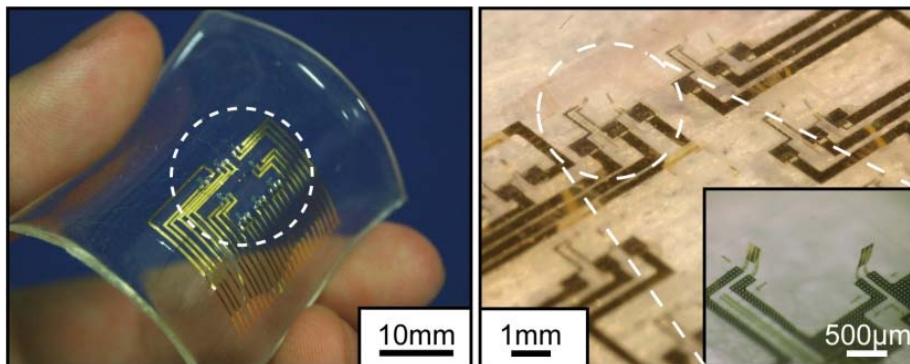
Flexible devices using rigid materials

Eiji Iwase (Waseda University)



Outline of my talk:

- **Importance:** Flexibility on energy components
- **Difference:** Bendability and stretchability
- **Challenge:** High performance and highly stretchable device



Importance : Flexible energy components

Energy generator (ex. solar cells, thermoelectric generators)

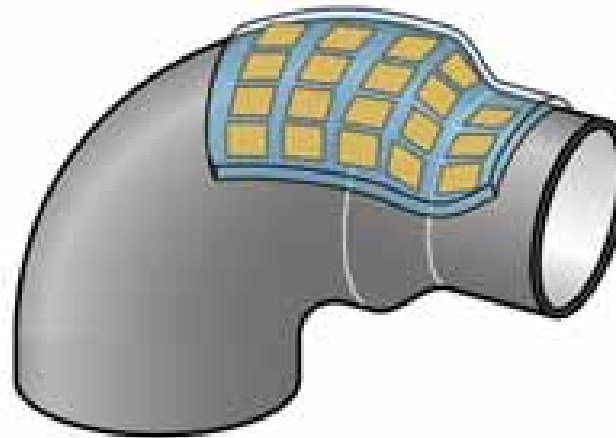
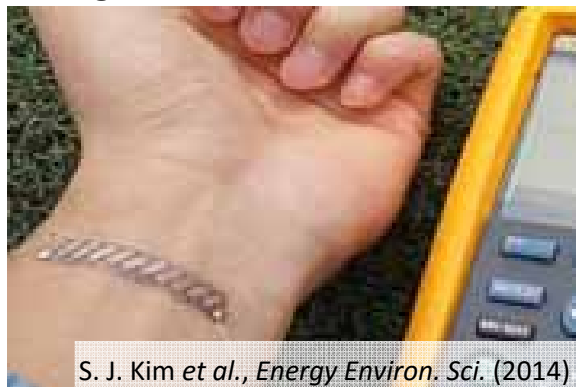
Flexible organic solar cell



Bendable CNT-based thermoelectric generator

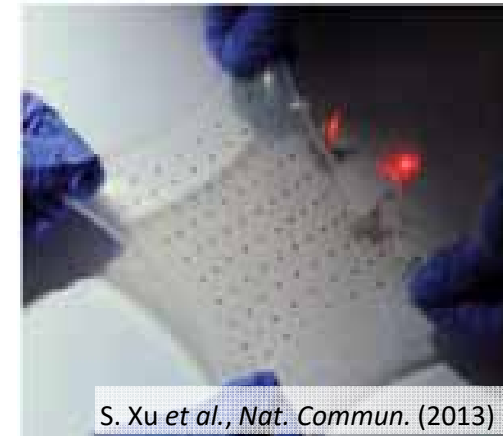


Bendable thermoelectric generator on a glass fabric

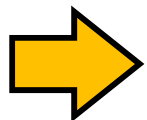
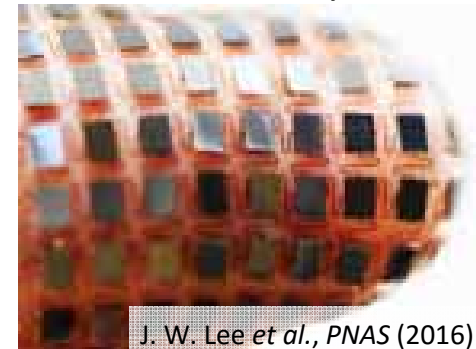


Energy storage (ex. Lithium-ion batteries)

Stretchable Lithium-ion battery



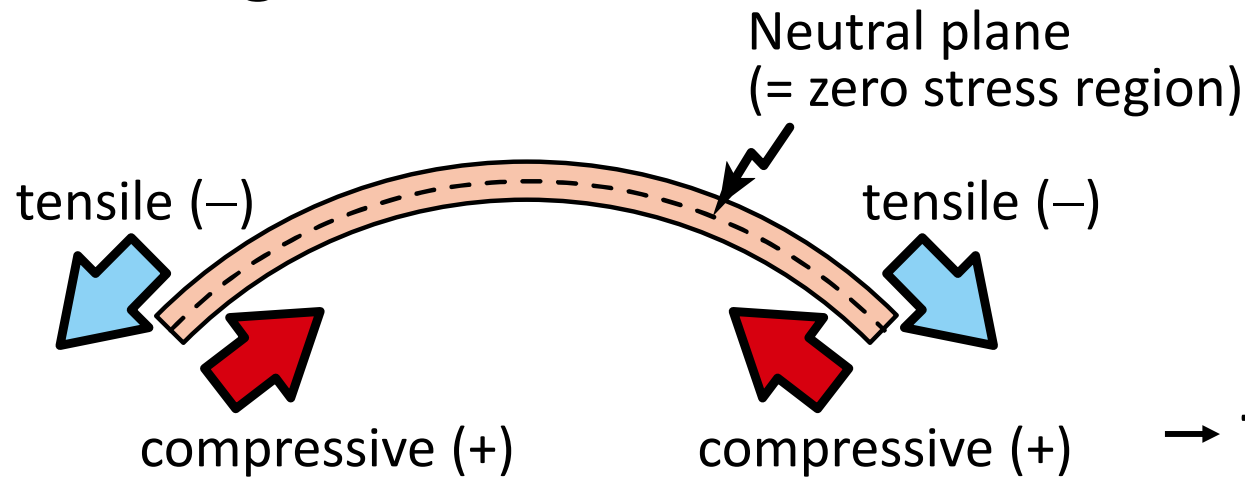
Lithium-ion battery sheet



To use on any curved surface, flexibility is very important!

Difference: Bendability and stretchability

(i) Bending deformation

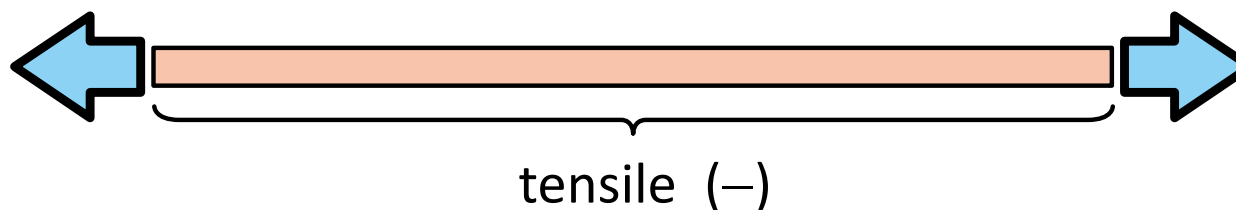


Ultrathin silicon solar cells



→ Thin device can have a bendability

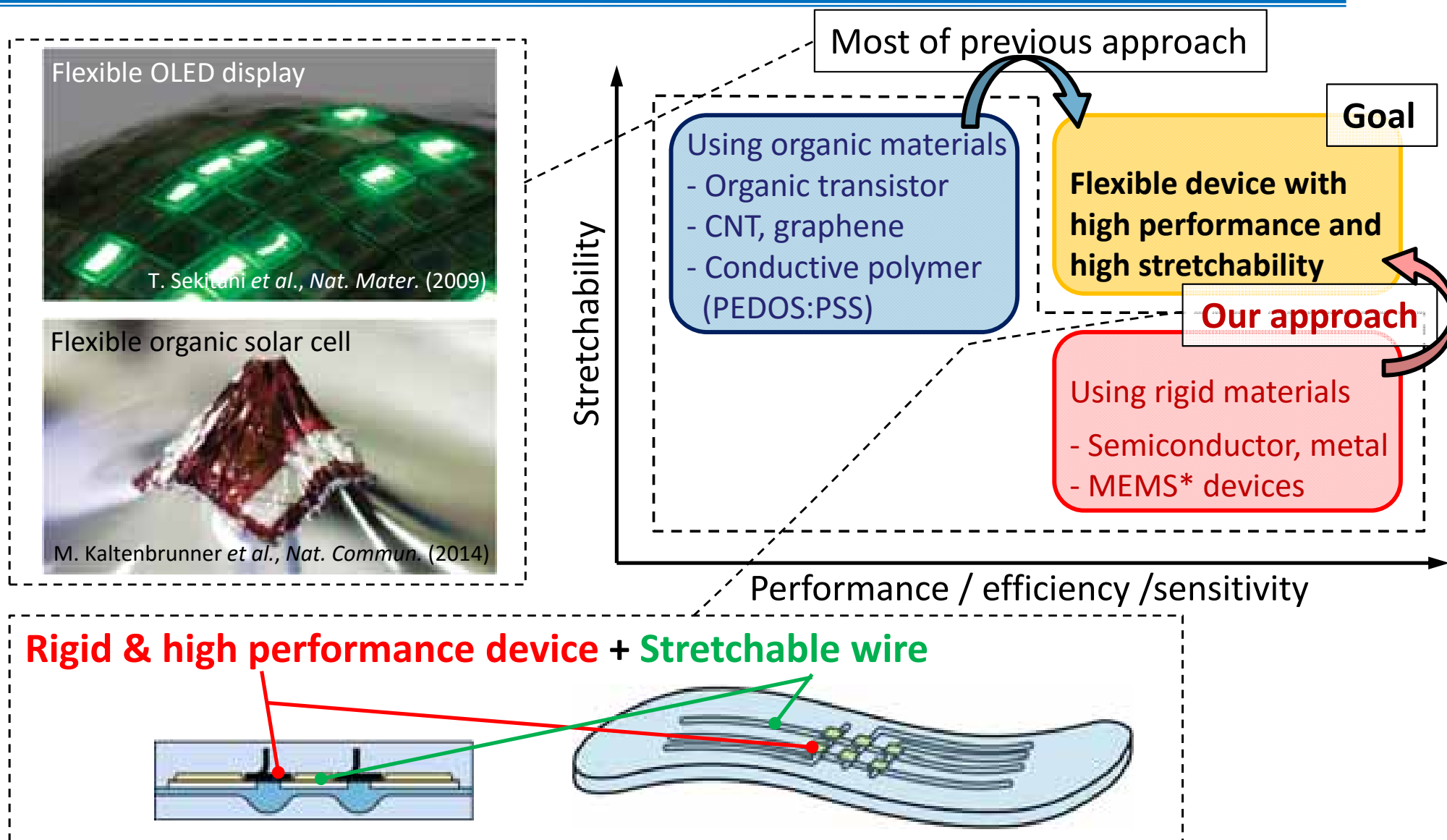
(ii) Stretching deformation



→ There is no obvious solution to avoid a fracture

➔ **Stretchability is a challenging and important issue on flexible device**

Challenge: Approach for stretchable device



* MEMS = Micro-Electro-Mechanical Systems
= Tiny (< 1 mm) electric sensor/actuator

Challenge: Approach for stretchable device

Rigid & high performance device + **Stretchable wire**

Functional part

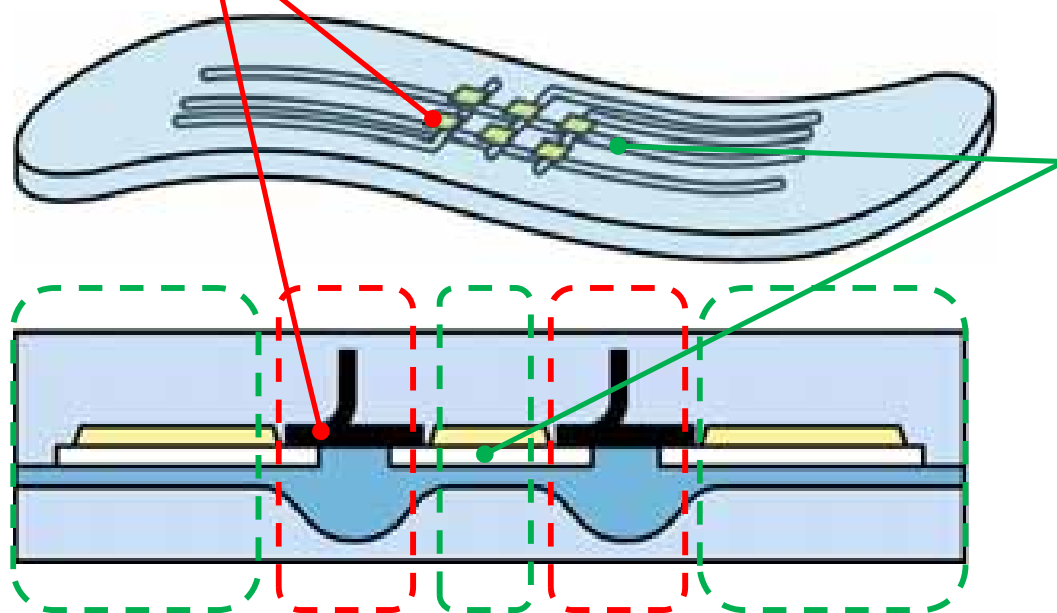
- Using MEMS devices or Silicon chips (for high performance or sensitivity)
- No deformation

1. Stamping transfer method

Wire part

- High stretchability
- Using metal (for high conductivity)
- Self-healing function

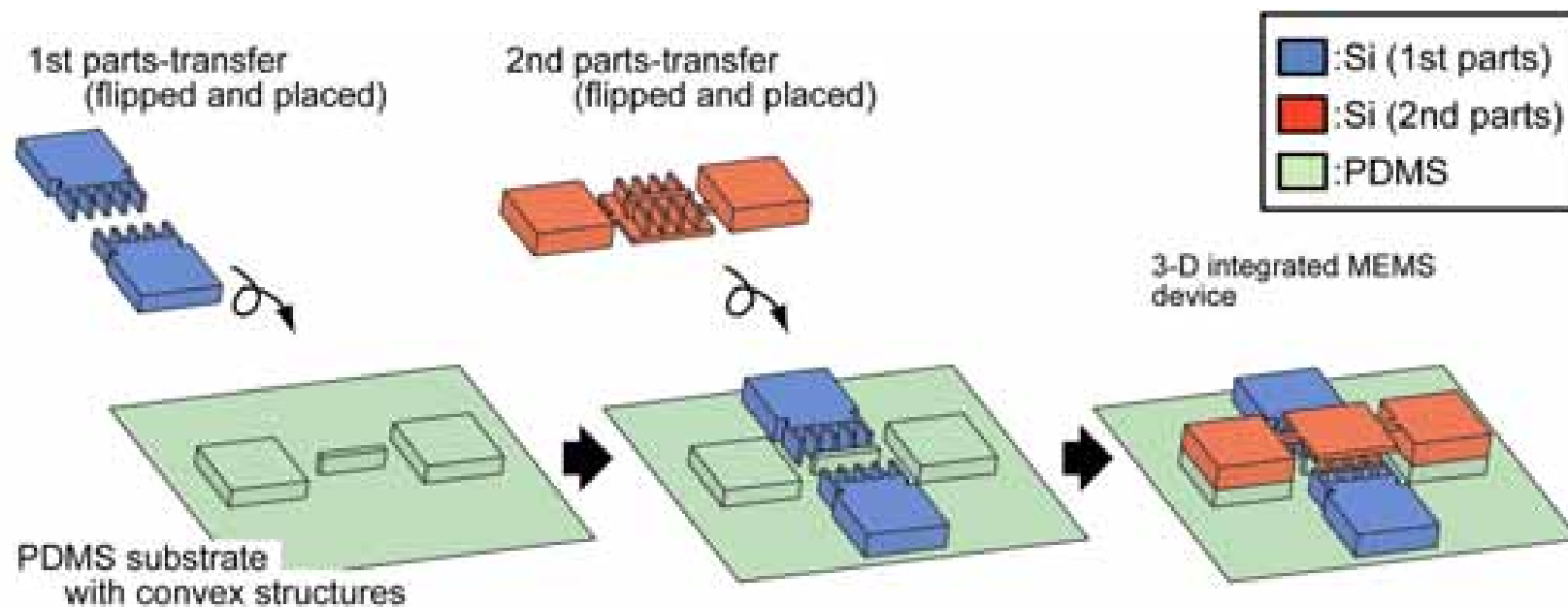
2. Self-healing metal wire



Small deformation region
Large deformation region

Stamping transfer method

- Transfer silicon parts of sensors or actuators directly onto flexible substrate



- Enable to fabricate Si-MEMS devices on a flexible substrate
- Enable to transfer multiple parts (ex. thermoelectric generators, piezoresistive sensors, electrostatic actuators, optical photodiodes)
- Build three-dimensional structures

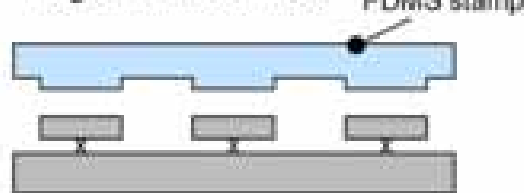
Stamping transfer method

Liftoff process

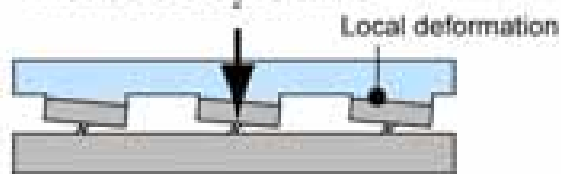
(A) Fabricate Si structures



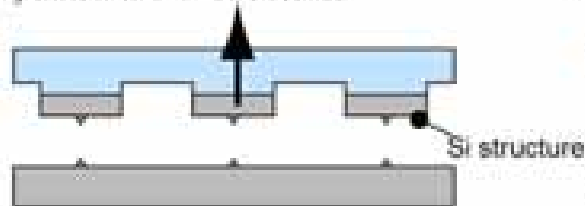
(B) Etch SiO₂ by HF
Align a PDMS sheet



(C) Press the PDMS sheet
Break the SiO₂ columns

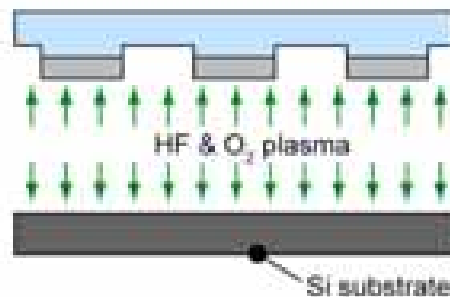


(D) Liftoff the Si structures

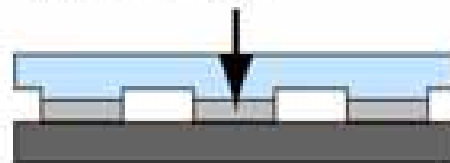


Stamping transfer process

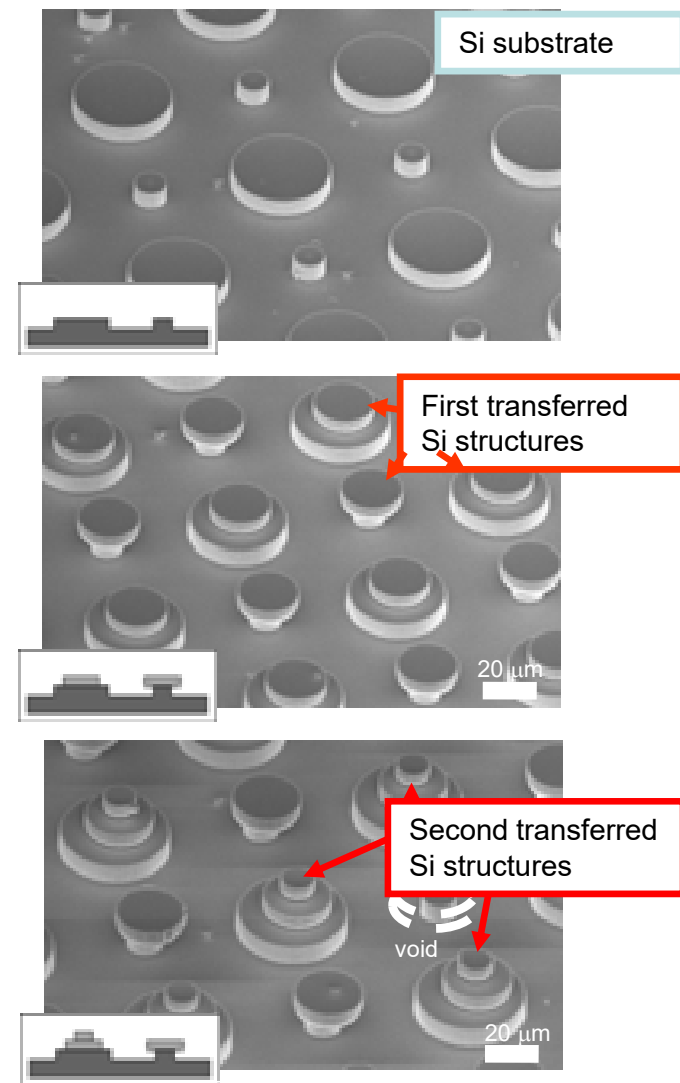
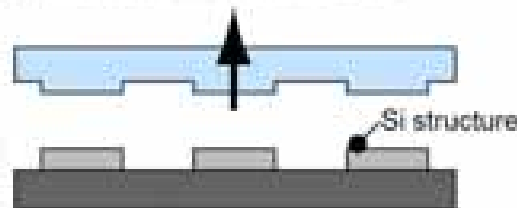
(E) Remove the SiO₂ by HF
Modify the surface by O₂ plasma



(F) Stamp the Si structures onto the Si substrate



(G) Transfer the Si structures



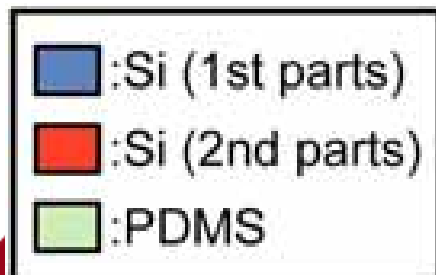
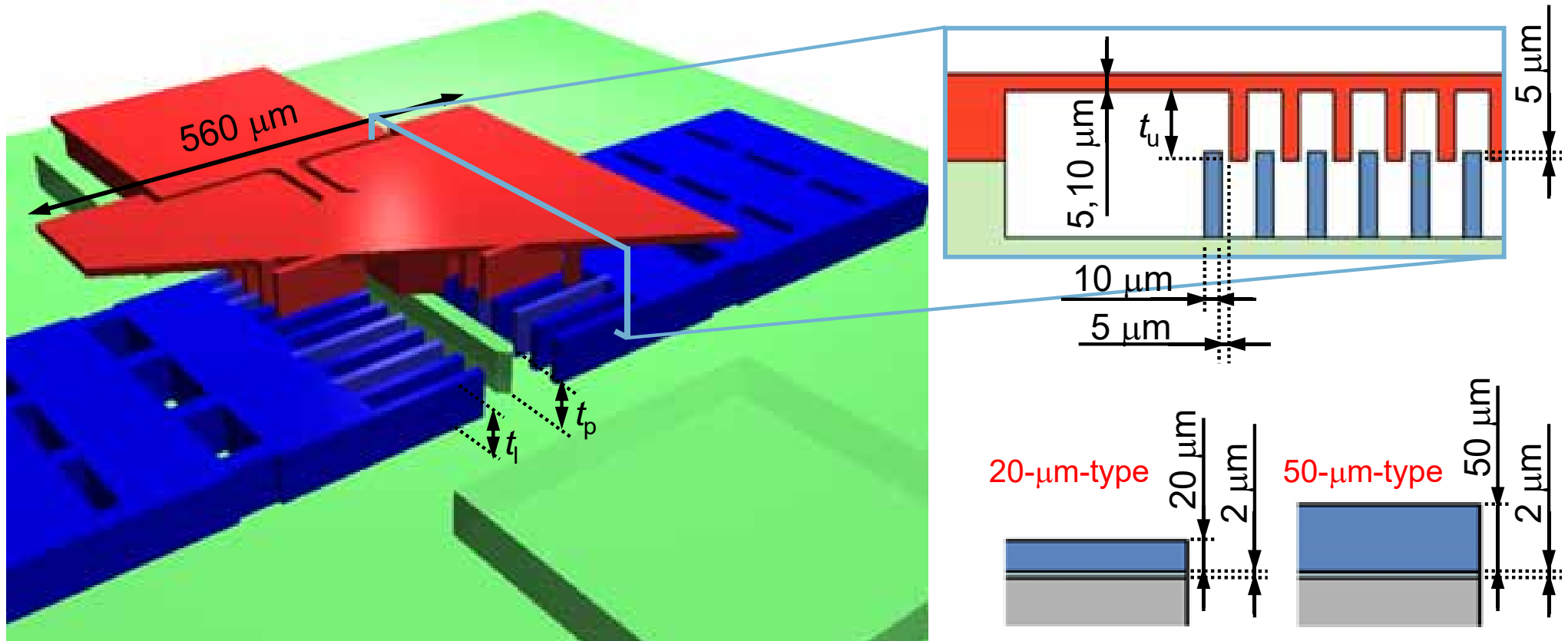
H. Onoe, E. Iwase, et al., *J. Micromech. Microeng.* (2007)



Transfer yield > 80%, Positioning error < $\pm 2 \mu\text{m}$



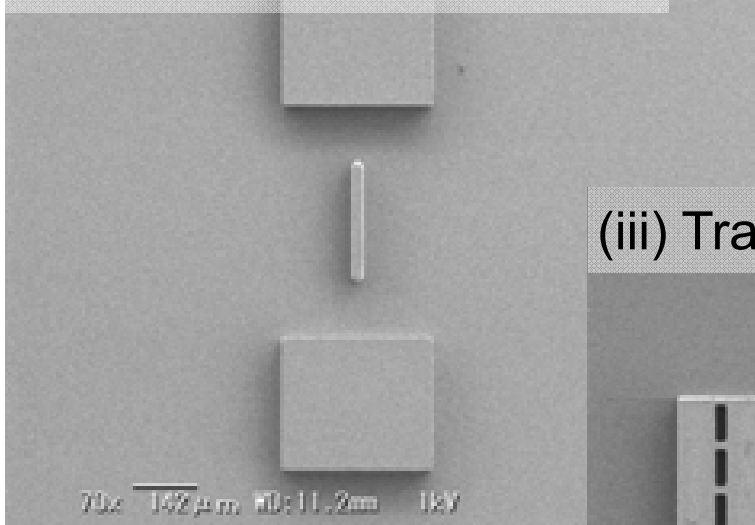
Design of micro scanning mirror



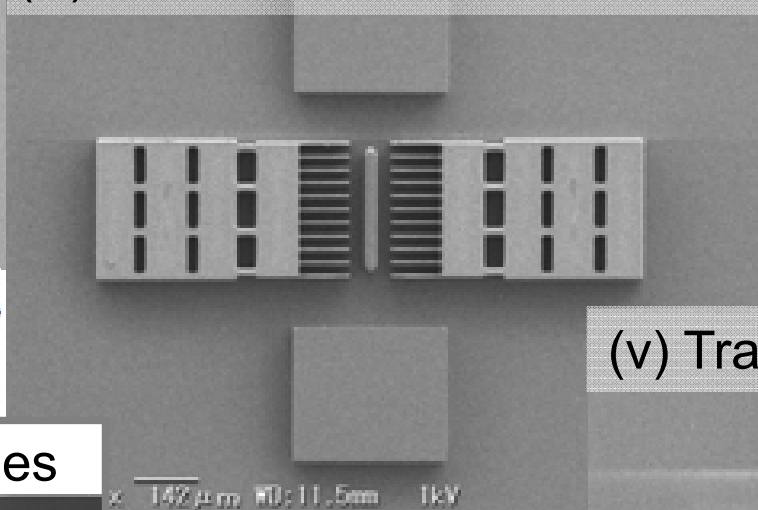
	20- μm -type	50- μm -type
lower electrodes thickness (t_l)	20 μm	50 μm
hidden electrodes thickness (t_u)	15 μm	40 μm
hidden PDMS spring height (t_s)	15 μm	45 μm
maximum tilt angle (θ_{max})	5.74 °	15.5 °

Fabrication process

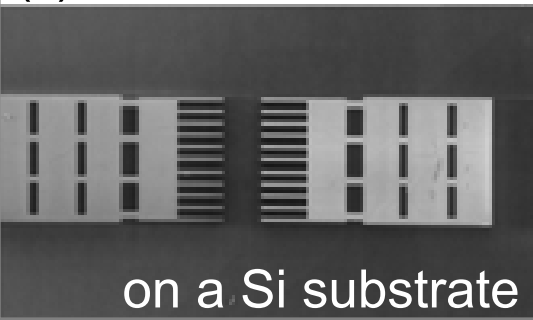
(i) PDMS flexible substrate



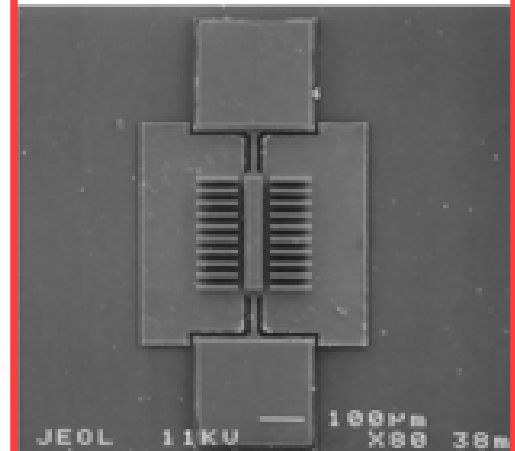
(iii) Transfer of lower electrodes



(ii) Lower electrodes

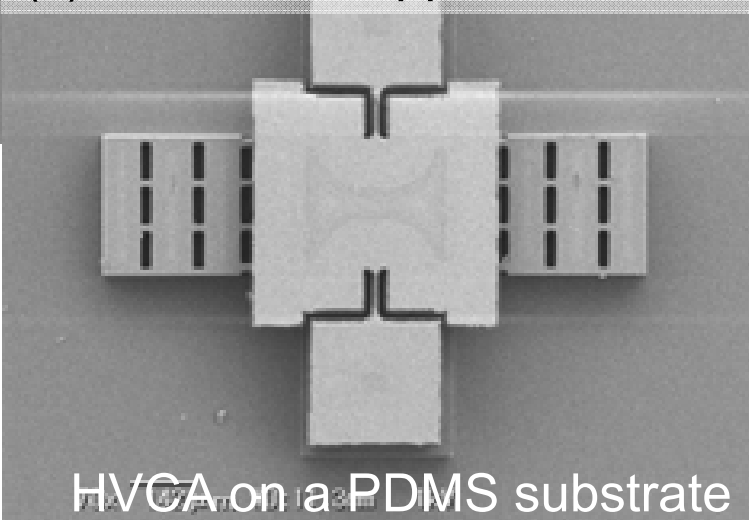


(iv) Upper electrode



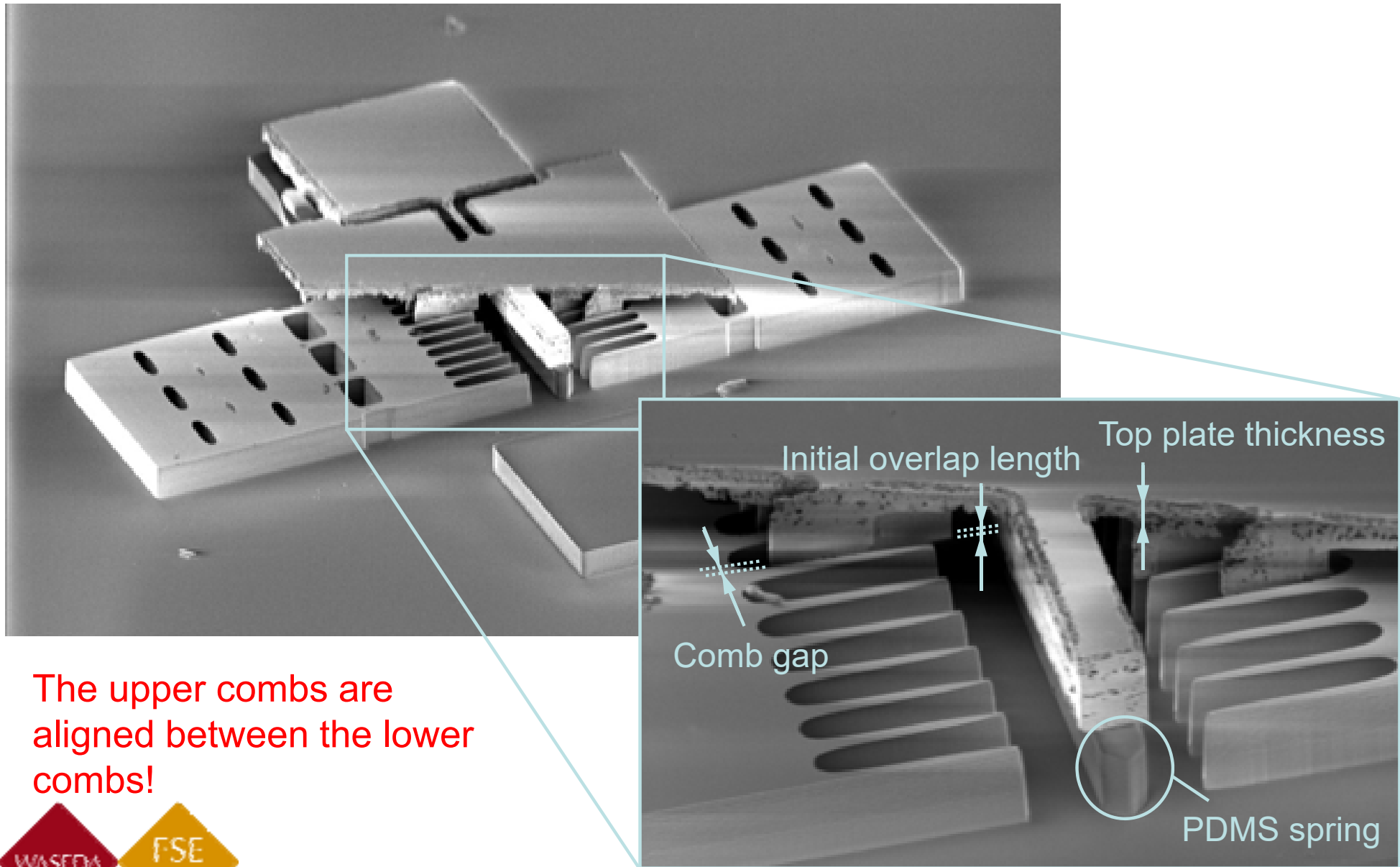
on a Si substrate

(v) Transfer of upper electrode

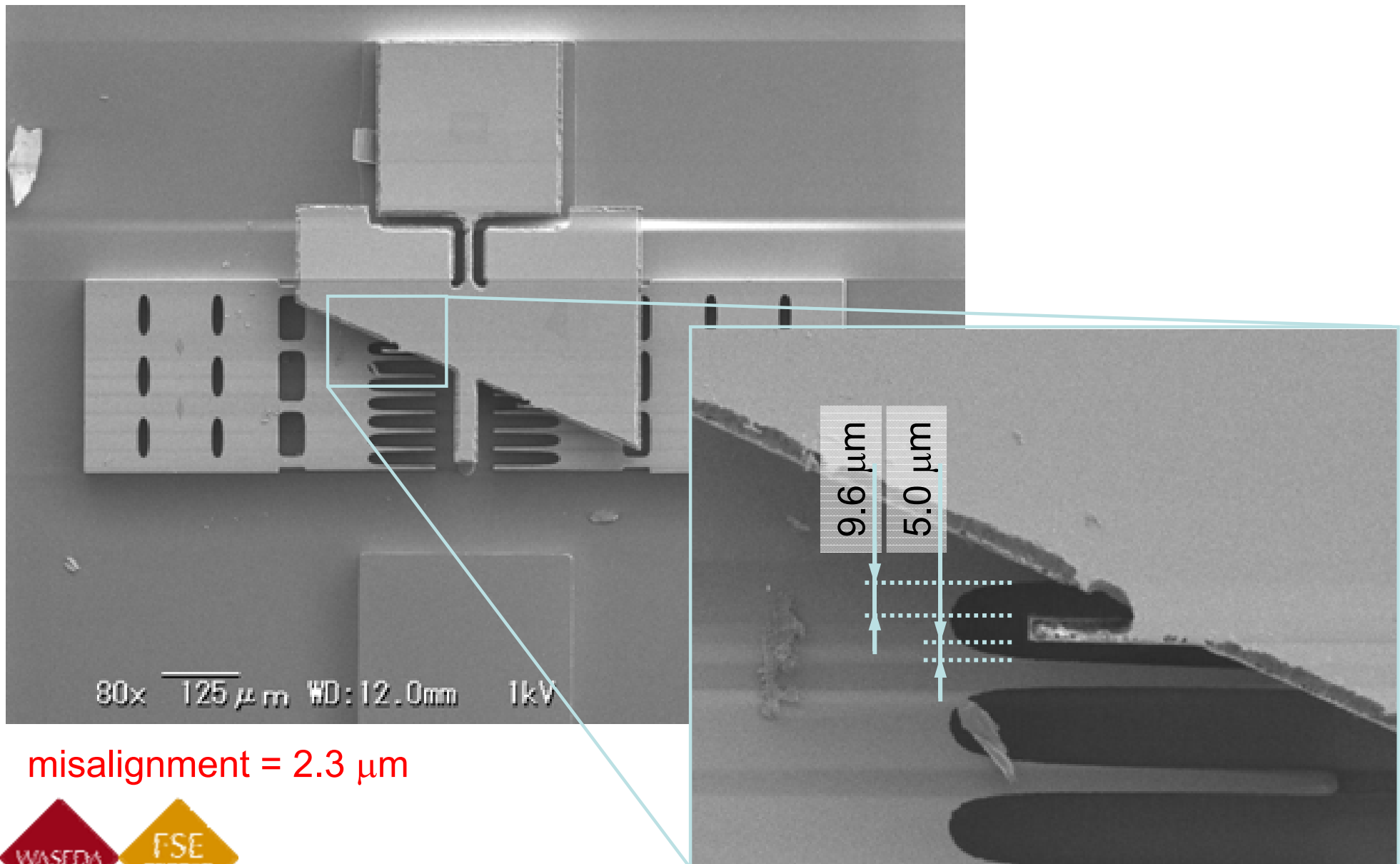


Simple process!

Cut model of micro scanning mirror

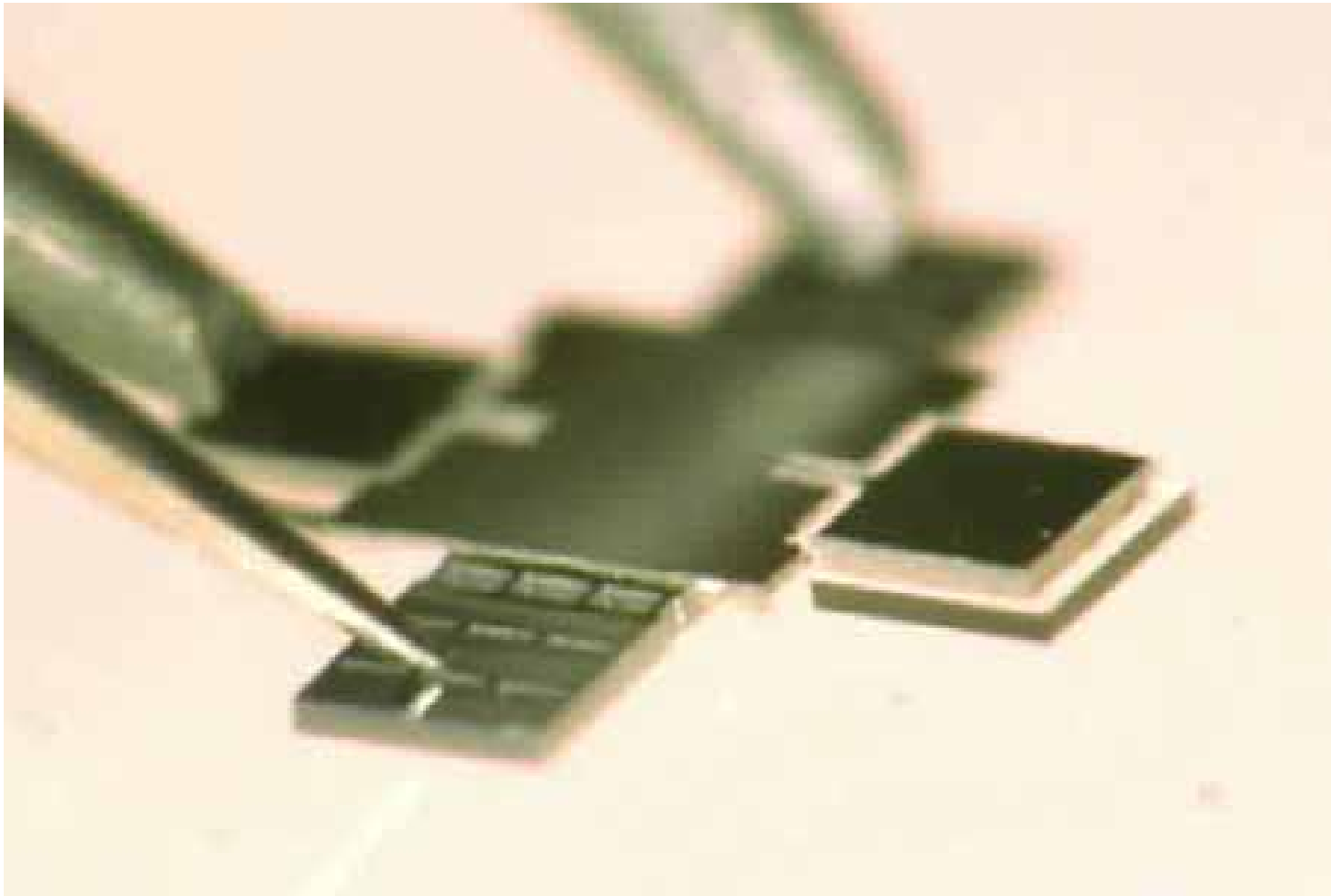


Cut model of micro scanning mirror



Actuation of micro scanning mirror

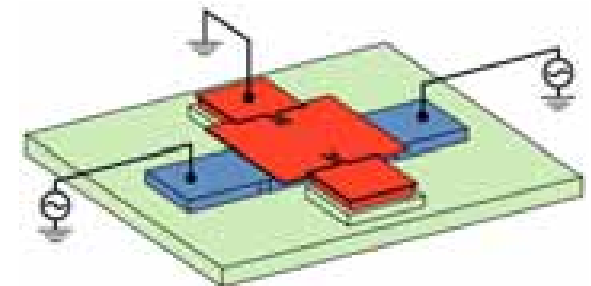
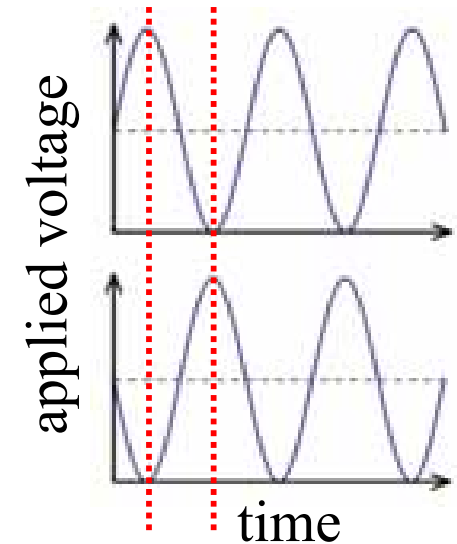
50- μm -type, $V = 300\text{ V}$, $f = 1 - 8\text{ Hz}$



$$V_u = \text{GND}$$

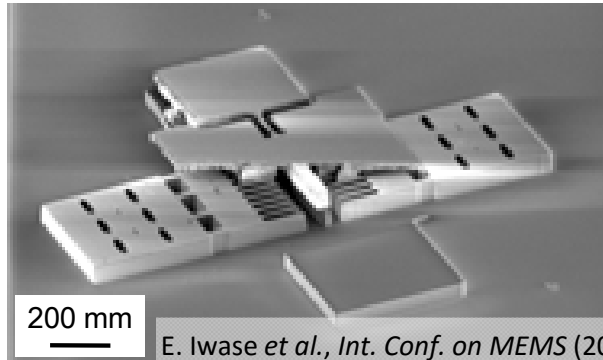
$$V_{11} = V_0/2(1 + \sin(2\pi ft))$$

$$V_{12} = V_0/2(1 - \sin(2\pi ft))$$

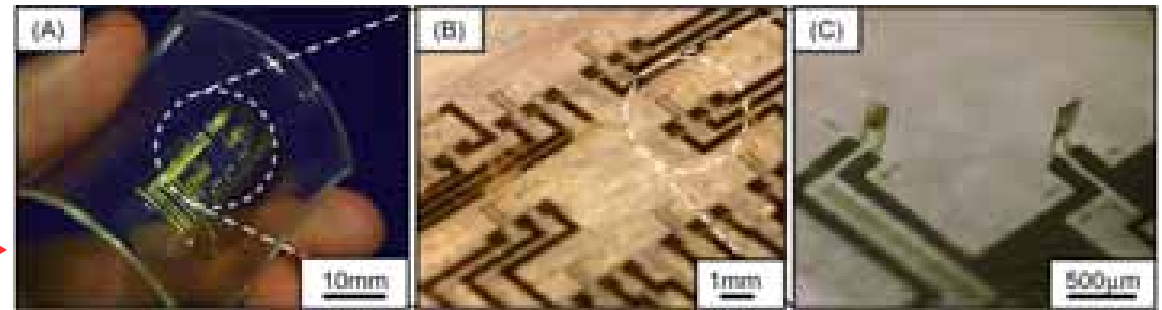


Applications of the stamping transfer method

Complex 3-D Structure & actuator on PDMS

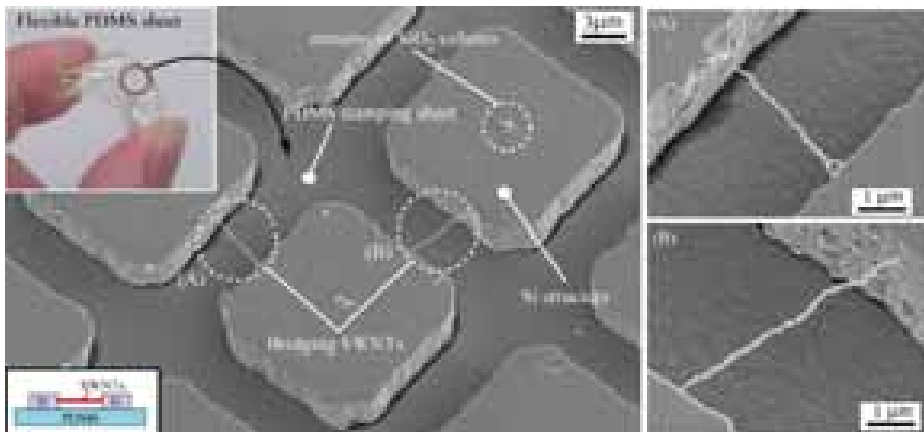
E. Iwase *et al.*, *Int. Conf. on MEMS* (2008)

Flexible Si-based Force Sensor



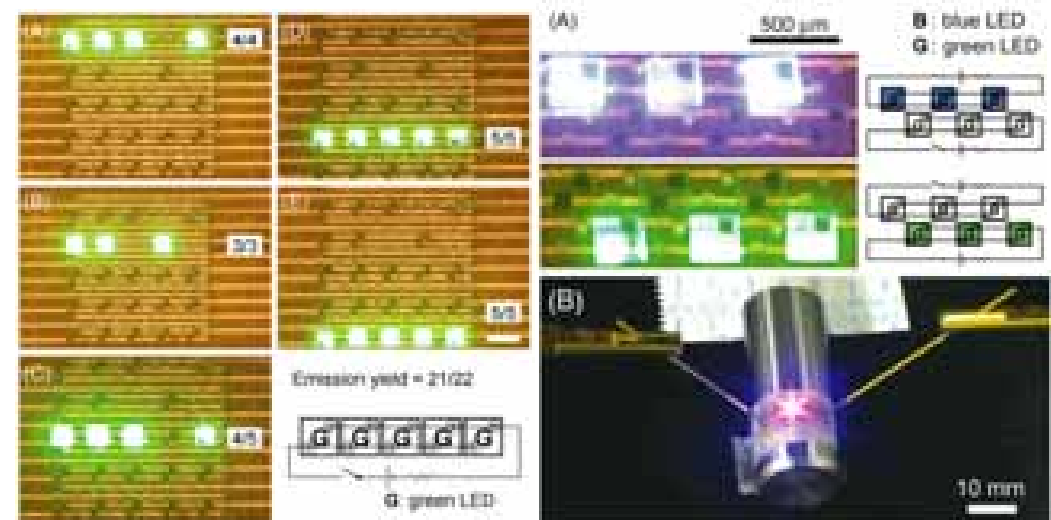
K. Noda, H. Onoe, E. Iwase, *et al.*, *J. Micromech. Microeng.* (2013)

Si block with CNT



Y. Taki, E. Iwase, *et al.*, *Int. Conf. on MEMS* (2009)

Flexible LED display



H. Onoe, A. Nakai, E. Iwase, *et al.*, *J. Micromech. Microeng.* (2009)

Challenge: Approach for stretchable device

Rigid & high performance device + **Stretchable wire**

Functional part

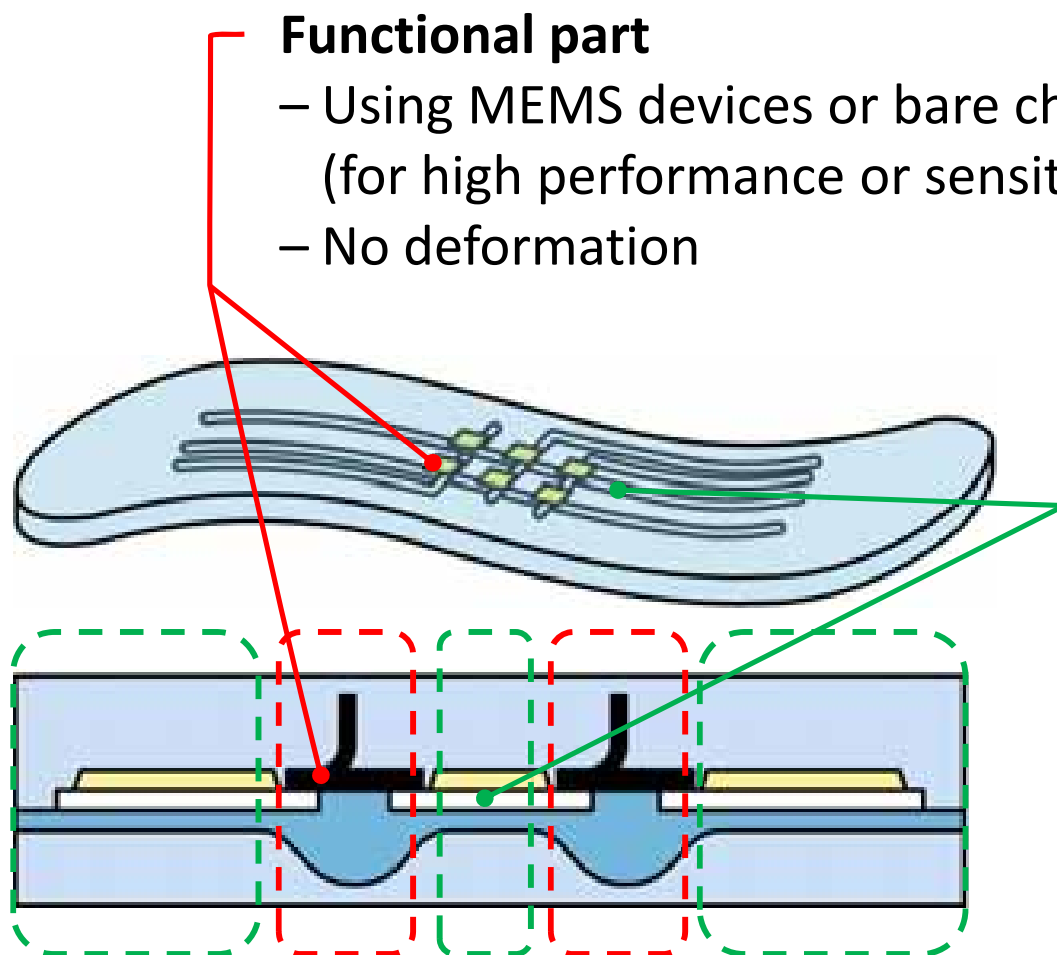
- Using MEMS devices or bare chip (for high performance or sensitivity)
- No deformation

1. Stamping transfer method

Wire part



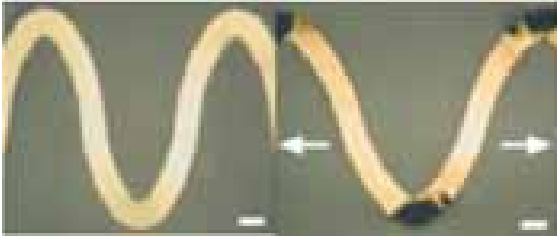

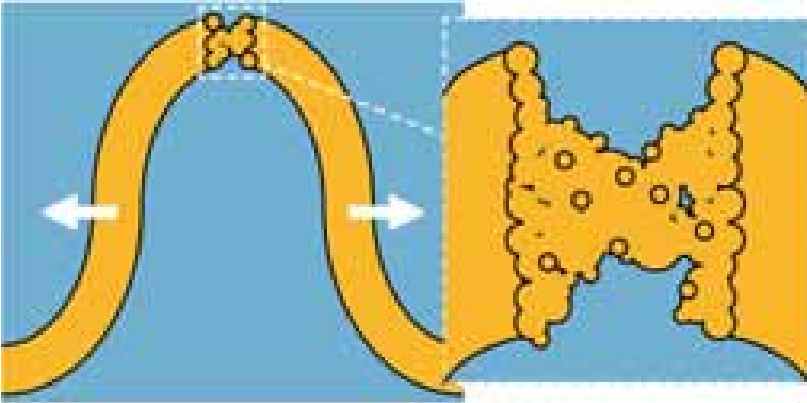



- High stretchability
- Using metal (for high conductivity)
- Self-healing function

2. Self-healing metal wire



Small deformation region
Large deformation region

Previous studies of flexible wire

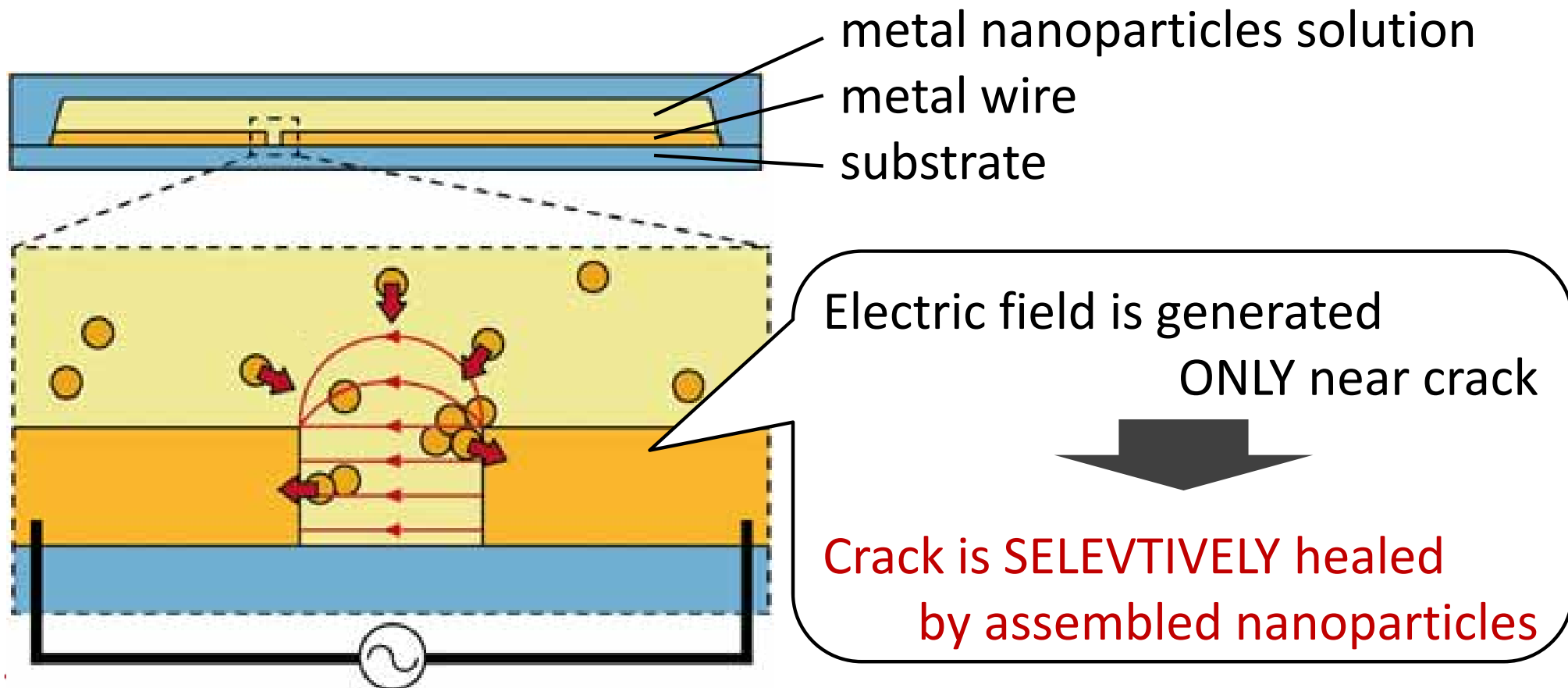
Flexible Wire		Conductivity	Flexibility
Material Conductive Elastomer Wire ¹ 		✕ $\sim 10^4$ S/m	
Shape Curved Metal Wire ² 		 10^7 S/m	cracking
Function  Curved Metal Wire + Self-Healing		  $\sim 10^7$ S/m	  Crack Healing

1. T. Sekitani *et al.*, *Nature Materials* (2009) 2. D. S. Gray *et al.*, *Adv. Mater.* (2004)

Self-healing metal wire

Providing self-healing function to metal wire

➡ Electric field trapping of gold nanoparticles



Analysis of Electric Field Trapping

Total force acting on nanoparticle near crack
(in the case of high frequency voltage)

$$\mathbf{F}_{\text{Total}} = \mathbf{F}_{\text{VDW}} + \mathbf{F}_{\text{ESR}} + \mathbf{F}_{\text{DEP}}$$

\mathbf{F}_{VDW} : Van der Waals force

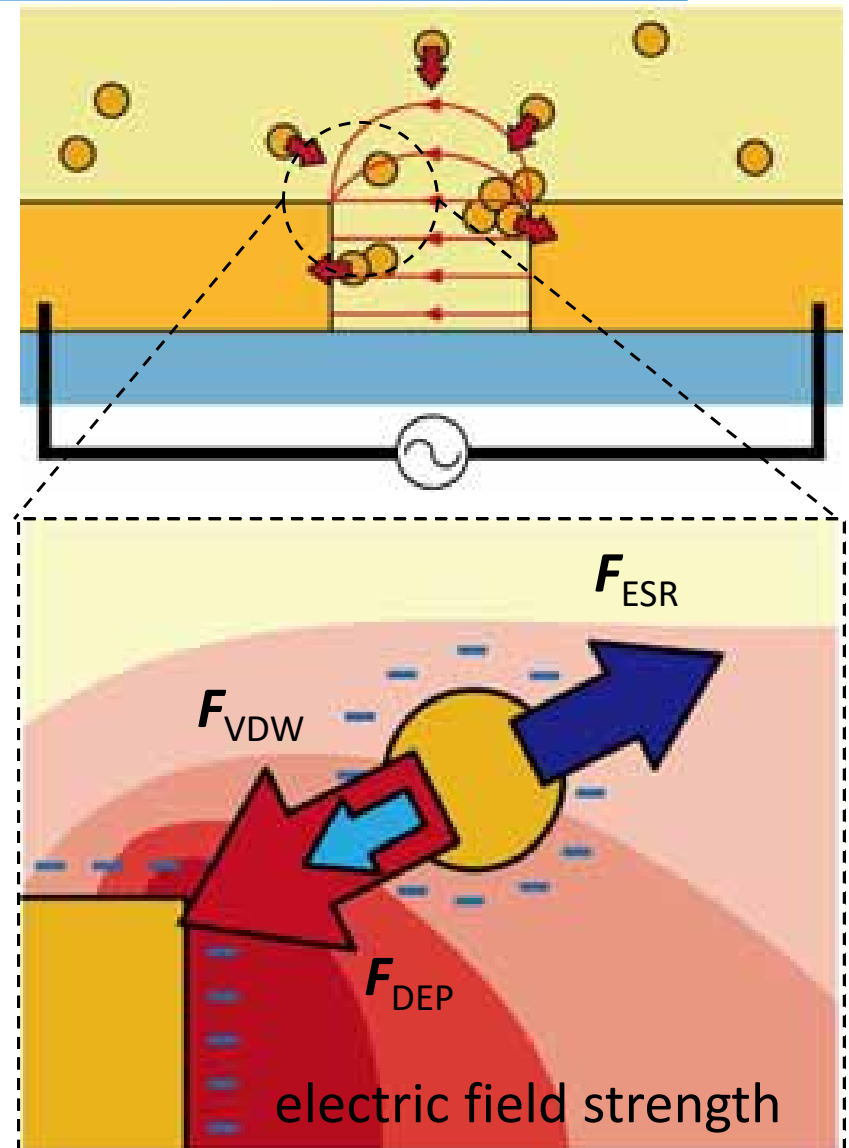
\mathbf{F}_{ESR} : Electrostatic repulsive force

determined by solution and particle

\mathbf{F}_{DEP} : Dielectrophoresis force

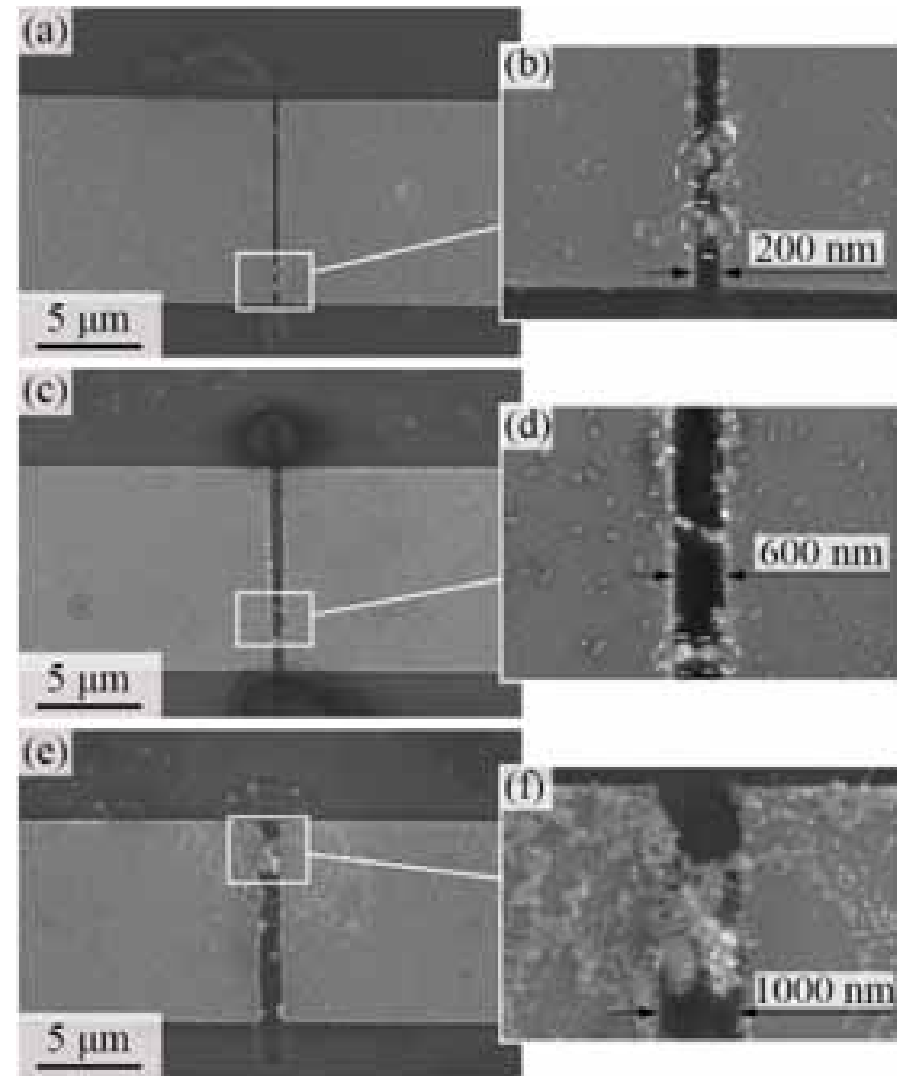
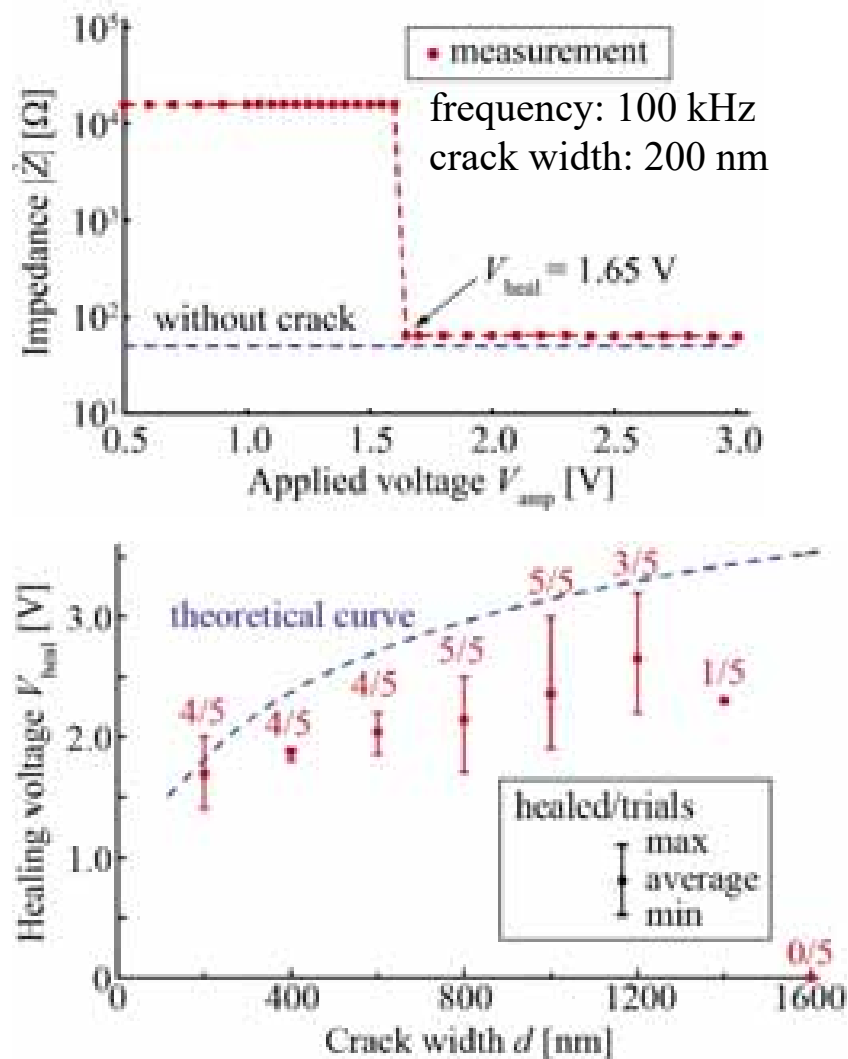
$$\langle \mathbf{F}_{\text{DEP}} \rangle = 2\pi\epsilon_1 r^3 \text{Re}[\underline{K}(\omega)] \nabla E_{\text{rms}}^2$$

determined by applied voltage



$\mathbf{F}_{\text{Total}}$ gets attractive near crack → electric field trapping

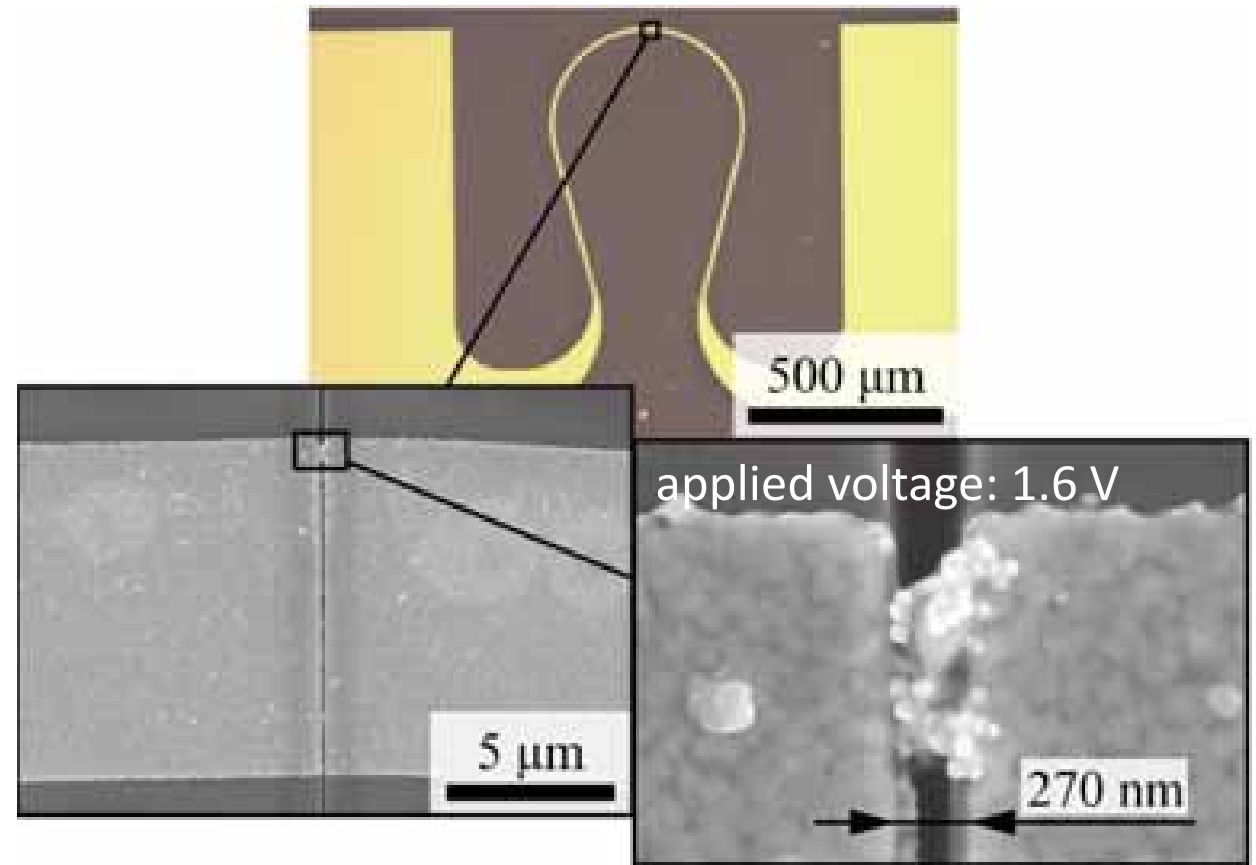
Self-healing on glass substrate



T. Koshi, E. Iwase, *Jpn. J. Appl. Phys* (2015)

Impedance dropped from $10^4 \Omega$ to $10^1 \Omega$ \Rightarrow Self-healing

Self-healing on Stretchable Substrate

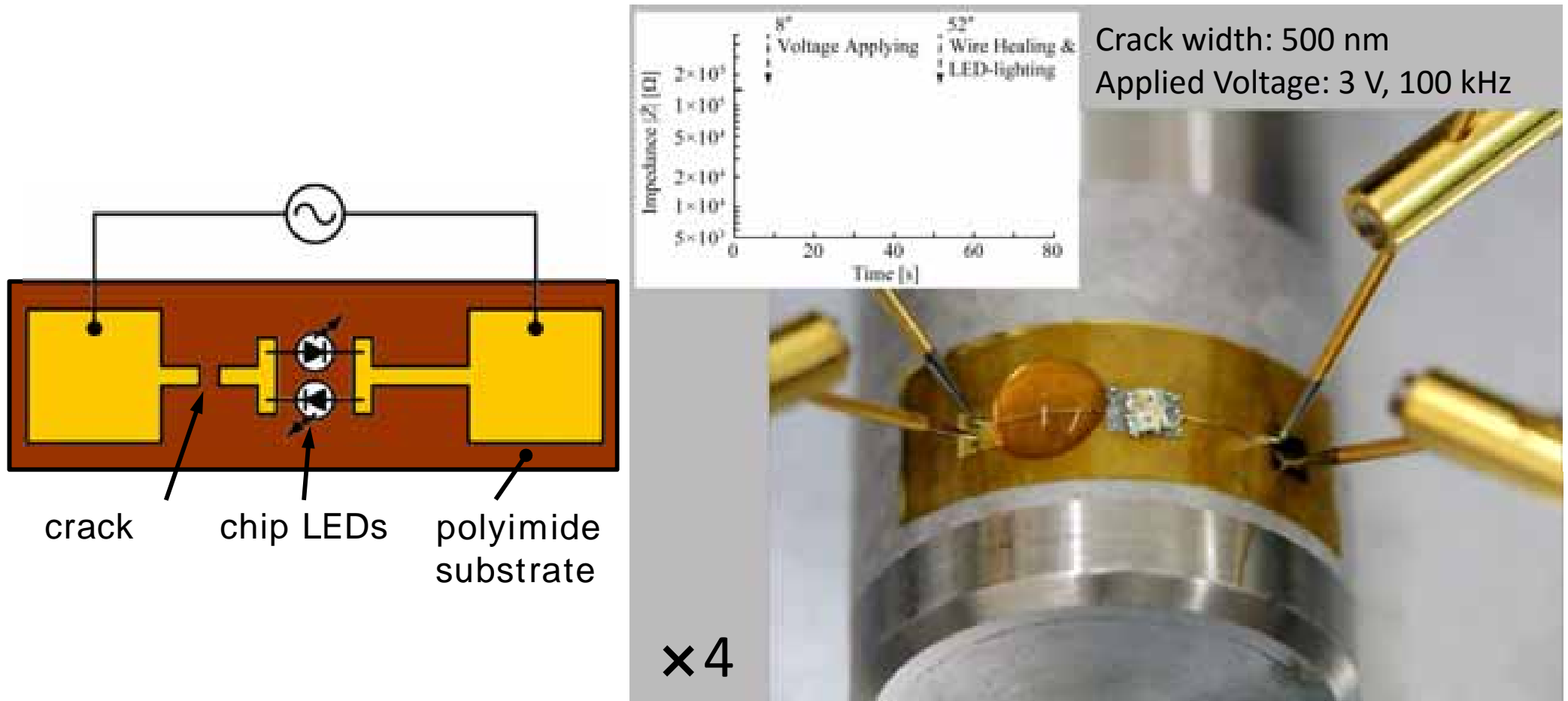


T. Koshi, E. Iwase, *Jpn. J. Appl. Phys* (2015)

Showing usefulness of
self-healing for flexible devices

Device application

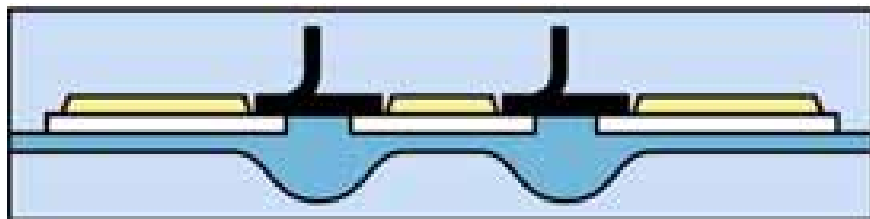
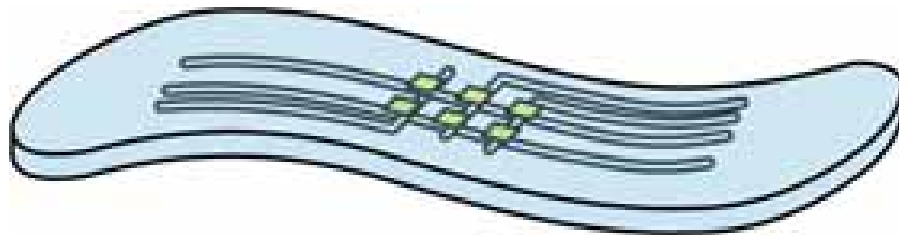
Flexible LED device on a curved surface ($r = 12.7 \text{ mm}$)



➡ Wire is healed and LEDs are emitted.

Conclusion

- We proposed a concept of flexible devices using rigid materials to achieve both high performance and high stretchability.



1. Stamping transfer method



2. Self-healing metal wire

